

100V NPN LOW SATURATION TRANSISTOR IN SOT23

Features

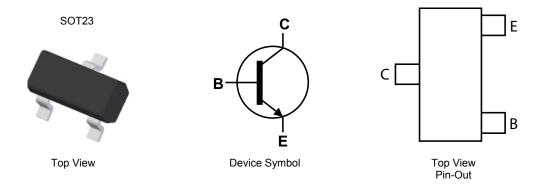
- BV_{CEO} > 100V
- BV_{CEX} > 170V forward blocking voltage
- BV_{ECO} > 6V reverse blocking voltage
- I_C = 3A high Continuous Collector Current
- Low saturation voltage, V_{CE(SAT)} < 80mV @1A
- $R_{CE(SAT)} = 67m\Omega$ for a low equivalent On-Resistance
- 1.25W Power dissipation
- hFE specified up to 3A for high current gain hold up
- Complementary PNP Type: ZXTP25100BFH
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: molded plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight 0.008 grams (approximate)

Applications

- Lamp relay and solenoid drivers
- General switching in automotive and industrial applications
- · Motor drive and control



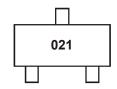
Ordering Information (Note 4)

ĺ	Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	ZXTN25100BFHTA	021	7	8	3,000

Notes:

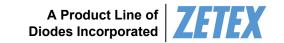
- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



021 = Product Type Marking Code





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	170	V
Collector-Emitter Voltage (Forward Blocking)	V _{CEX}	170	V
Collector-Emitter Voltage	V _{CEO}	100	V
Emitter-Base Voltage (Reverse Blocking)	V _{ECO}	6	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	3	Α
Peak Pulse Current (Note 5)	I _{CM}	9	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation Linear Derating Factor	(Note 5)	P _D	0.73 5.84	mW
Power Dissipation Linear Derating Factor	(Note 6)	P _D	1.05 8.4	mW
Power Dissipation Linear Derating Factor	(Note 7)	P _D	1.25 9.6	mW
Power Dissipation Linear Derating Factor	(Note 8)	P _D	1.81 14.5	mW
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	171	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	R _{0JA}	119	°C/W
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	100	°C/W
Thermal Resistance, Junction to Ambient	(Note 8)	$R_{\theta JA}$	69	°C/W
Thermal Resistance, Junction to Leads (Note 9)		R _{0JL}	74.96	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C	

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	≥ 8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

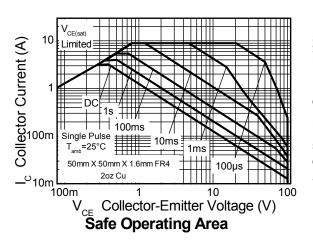
Notes:

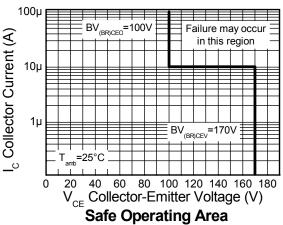
- 5. For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. Same as note (5), except mounted on 25mm x 25mm x 1.6mm FR4 PCB with 2 oz copper. 7. Same as note (5), except mounted on 50mm x 50mm x 1.6mm FR4 PCB with 2 oz copper.

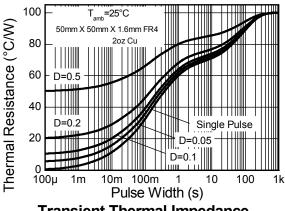
- 8. Same as note (7), except measured at t < 5secs.
 9. Thermal resistance from junction to solder-point (at the end of collector lead).
 10.Refer to JEDEC specification JESD22-A114 and JESD22-A115.

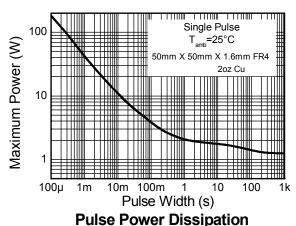


Thermal Characteristics and Derating information

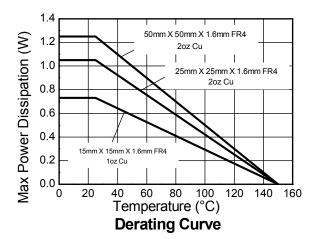








Transient Thermal Impedance







Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

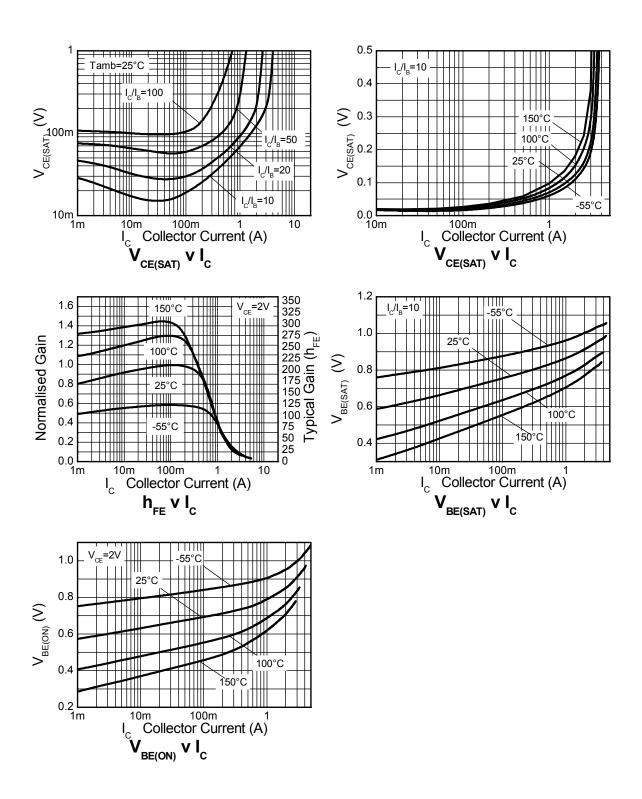
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_CBO	170	220	-	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Forward Blocking) (Note 11)	BV _{CEX}	170	210	-	V	I_C = 100μA, R_{BE} < 1k Ω or -1V < V_{BE} < 0.25V
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	100	120	-	V	I _C = 1mA
Emitter-Collector Breakdown Voltage (Reverse Blocking) (Note 11)	BV _{ECX}	6	7	-	V	I_E = 100μA, R_{BC} < 1k Ω or 0.25V > V_{BC} > -0.25V
Emitter-Collector Breakdown Voltage	BV _{ECO}	6	8.4	-	V	I _E = 100μA
Emitter-Base Breakdown Voltage	BV_{EBO}	7	8	-	V	I _E = 100μA
Collector Cut-off Current	I _{CBO}	-	<1	50 20	nA	V _{CB} = 136V V _{CB} = 136V, T _A = +100°C
Collector Emitter Cut-off Current	I _{CEX}	-	-	100	nA	V_{CE} = 136V, R_{BE} < 1kΩ or -1V < V_{BE} < 0.25V
Emitter Cut-off Current	I _{EBO}	-	<1	50	nA	V _{EB} = 5.6V
Static Forward Current Transfer Ratio (Note 11)	h _{FE}	100 50 -	200 85 20	300 - -	-	$I_C = 10 \text{mA}, V_{CE} = 2V$ $I_C = 1 \text{A}, V_{CE} = 2V$ $I_C = 3 \text{A}, V_{CE} = 2V$
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	- - -	40 100 70 200	55 135 80 250	mV	$I_C = 0.5A$, $I_B = 50mA$ $I_C = 0.5A$, $I_B = 10mA$ $I_C = 1A$, $I_B = 100mA$ $I_C = 3A$, $I_B = 300mA$
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	-	940	1050	mV	I _C = 3A, I _B = 300mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(on)}	-	890	1000	mV	I _C = 3A, V _{CE} = 2V
Transition Frequency	f _T	-	160	-	MHz	I _C = 100mA, V _{CE} = 5V, f = 100MHz
Collector Output Capacitance	C_{obo}	-	9.4	20	pF	V _{CB} = 10V, f = 1MHz
Delay Time	t _(d)	-	16	-	ns	
Rise Time	$t_{(r)}$	-	55	-	ns	$V_{CC} = 10V, I_C = 0.5A,$
Storage Time	t _(s)	-	677	-	ns	I _{B1} = -I _{B2} = 50mA
Fall Time	t _(f)	-	95	-	ns	<u> </u>

Notes: 11. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$





Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

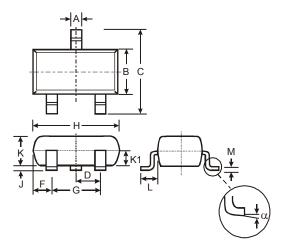






Package Outline Dimensions

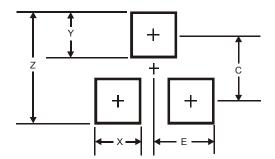
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
7	0.013	0.10	0.05		
K	0.903	1.10	1.00		
K1	-	-	0.400		
L	0.45	0.61	0.55		
М	0.085	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
Z	2.9		
X	8.0		
Y	0.9		
С	2.0		
ш	1.35		





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